

HIGH POWER GALLIUM NITRIDE SCHOTTKY RECTIFIER

Abstract of the Disclosure

A Schottky high power rectifier having a nitride insulator formed on the surface of a GaN substrate. The nitride insulator increases the electric field breakdown suppression at or near the surface of the rectifier below the insulator. In a preferred embodiment, the nitride insulator is an epitaxially grown aluminum nitride insulator.

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